NSN 5962-00-007-4100

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D - J.	 nath:

Between 0.750 inches and 0.795 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.120 inches and 0.195 inches

Maximum Power Dissipation Rating:

650.0 milliwatts

Operating Tempurature Range:

+0.0/+70.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs and w/decoded output and w/enable and w/open collector and w/storage

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

-0-001-ag joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-1.5 volts power source and 5.5 volts power source

Time Rating Per Chacteristic:

60.00 nanoseconds propagation delay time, low to high level output and 60.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Ram

Memory Capacity:

Unknown

Test Data Document:

07421-349-113-089 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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